

# High voltage fast-switching NPN power transistor

#### **Features**

- High voltage capability
- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed

#### **Description**

The device is manufactured using high voltage multi-epitaxial planar technology for high switching speeds and high voltage capability. It uses a cellular emitter structure with planar edge termination to enhance switching speeds. The device is designed for use as PFC in high frequency ballast half bridge voltage fed topology.

### **Applications**

- Electronic ballast for fluorescent lighting
- Dedicated for PFC solution in half-bridge voltage fed topology.

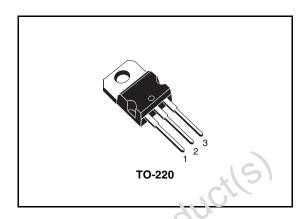


Figure 1. Internal scheniatic diagram

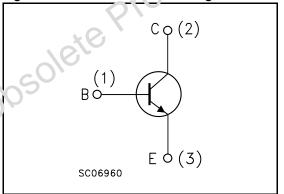


Table 1. Device summary

Order code Marking		Package	Packaging		
BUL805	BUL805	TO-220	Tube		

July 2008 Rev 2 1/8

#### **Contents**

1	Electrical ratings	3
2	Electrical characteristics	4
3	Package mechanical data	5
4	Revision history	7

Obsolete Product(s). Obsolete Product(s)

BUL805 Electrical ratings

# 1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V <sub>CES</sub>	Collector-emitter voltage (V <sub>BE</sub> = 0)	800	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	450	٧
V <sub>EBO</sub>	Emitter-base voltage (I <sub>C</sub> = 0)	9	٧
I <sub>C</sub>	Collector current	5	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5ms)	10	Α
I <sub>B</sub>	Base current	2	Α
I <sub>BM</sub>	Base peak current (t <sub>P</sub> < 5ms)	4	Α
P <sub>tot</sub>	Total dissipation at T <sub>C</sub> = 25°C	80	W
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

	Symbol	Parameter		Value	Unit	
	R <sub>thj-case</sub> R <sub>thj-amb</sub>	Thermal resistance junction-case Thermal resistance junction-amb	max max	1.56 62.5	°C/W	
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Electrical characteristics BUL805

## 2 Electrical characteristics

(T<sub>case</sub> = 25 °C unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector cut-off current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 800 V V <sub>CE</sub> = 800 V T <sub>C</sub> = 125 °C	:		100 500	μ <b>Α</b> μ <b>Α</b>
I <sub>CEO</sub>	Collector cut-off current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 450 V			250	μΑ
V <sub>EBO</sub>	Emitter-base voltage $(I_C = 0)$	I <sub>E</sub> = 10 mA	9			V
V <sub>CEO(sus)</sub> (1)	Collector-emitter sustaining voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10 mA	450			V
V <sub>CE(sat)</sub> (1)	Collector-emitter saturation voltage	$\begin{split} I_C &= 1 \text{ A} & I_B &= 0.2 \text{ A} \\ I_C &= 2 \text{ A} & I_B &= 0.4 \text{ A} \\ I_C &= 3 \text{ A} & I_B &= 0.6 \text{ A} \end{split}$	010	90	0.4 0.6 0.8	V V V
V <sub>BE(sat)</sub> (1)	Base-emitter saturation voltage	$\begin{split} I_C &= 1 \text{ A} & I_B &= 0.2 \text{ A} \\ I_C &= 2 \text{ A} & I_B &= 0.4 \text{ A} \\ I_C &= 3 \text{ A} & I_B &= 0.6 \text{ A} \end{split}$			1.1 1.3 1.5	V V V
h <sub>FE</sub>	DC current gain	$I_C = 10 \text{ mA}$ $V_{CE} = 5 \text{ V}$ $I_C = 2 \text{ A}$ $V_{CE} = 5 \text{ V}$	10 10		20	

<sup>(1)</sup> Pulsed duration = 300 μs, duty cycle ≤ 1.5%

## 3 Package mechanical data

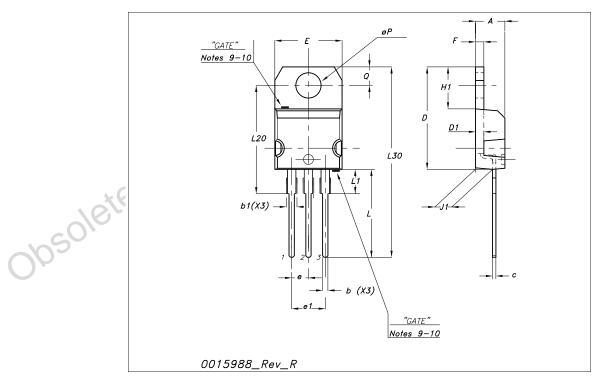
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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**577** 

#### TO-220 mechanical data

Dim	mm			inch		
DIM	Min	Тур	Max	Min	Тур	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



BUL805 Revision history

# 4 Revision history

Table 5. Document revision history

Date	Revision	Changes	
19-May-2006	1	Initial release.	
15-Jul-2008	2	Document status promoted from preliminary data to datasheet.	



**477** 

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**577**